

Abstract

A method of manufacturing a layer sequence and a method of  
5 manufacturing an integrated circuit

A method of manufacturing a layer sequence having a first and  
a second laterally confined structure comprises the steps of  
providing a first layer on a first surface portion of a  
10 substrate, which first layer is doped with dopant of a first  
type of conductivity, providing a second layer on a second  
surface portion of the substrate, which second layer is free  
of dopant of the first type of conductivity, forming a third  
layer on the first layer, which third layer is free of dopant  
15 of the first type of conductivity, and forming a fourth layer  
on the second layer, which forth layer is doped with dopant  
of the first type of conductivity. The first layer and the  
third layer are etched, thereby patterning the first and  
third layer to form the first laterally confined structure.  
20 The second layer and the forth layer are etched, thereby  
patterning the second and fourth layer to form the second  
laterally confined structure.